


# BCR8CS

MEDIUM POWER USE

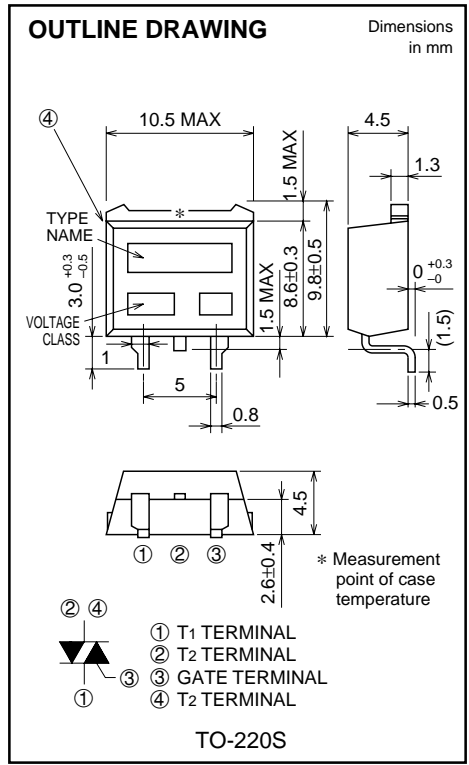
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

Refer to the page 6 as to the product guaranteed maximum junction temperature 150°C

**BCR8CS**



- **IT (RMS)** ..... **8A**
- **VDRM** ..... **600V**
- **IFGT I , IRGT I , IRGT III** ..... **20mA**



## APPLICATION

Solid state relay, hybrid IC

## MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		12	600	
VDRM	Repetitive peak off-state voltage *1	600		V
VDSM	Non-repetitive peak off-state voltage *1	720		V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, Tc=105°C*3	8	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	80	A
I <sup>2</sup> t	I <sup>2</sup> t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	26	A <sup>2</sup> s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
VGM	Peak gate voltage		10	V
IGM	Peak gate current		2	A
Tj	Junction temperature		-40 ~ +125	°C
Tstg	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	1.2	g

\*1. Gate open.

# BCR8CS

Refer to the page 6 as to the product guaranteed maximum junction temperature 150°C

**MEDIUM POWER USE**  
**NON-INSULATED TYPE, PLANAR PASSIVATION TYPE**

## ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDRM	Repetitive peak off-state current	T <sub>j</sub> =125°C, V <sub>DRM</sub> applied	—	—	2.0	mA	
V <sub>TM</sub>	On-state voltage	T <sub>c</sub> =25°C, I <sub>TM</sub> =12A, Instantaneous measurement	—	—	1.5	V	
V <sub>FGT I</sub>	Gate trigger voltage *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	1.5	V
V <sub>RGT I</sub>			II	—	—	1.5	V
V <sub>RGT III</sub>			III	—	—	1.5	V
I <sub>FGT I</sub>	Gate trigger current *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	20	mA
I <sub>RGT I</sub>			II	—	—	20	mA
I <sub>RGT III</sub>			III	—	—	20	mA
V <sub>GD</sub>	Gate non-trigger voltage	T <sub>j</sub> =125°C, V <sub>D</sub> =1/2V <sub>DRM</sub>	0.2	—	—	V	
R <sub>th (j-c)</sub>	Thermal resistance	Junction to case *3 *4	—	—	2.0	°C/W	
(dv/dt) <sub>c</sub>	Critical-rate of rise of off-state commutating voltage *5	T <sub>j</sub> =125°C	10	—	—	V/μs	

\*2. Measurement using the gate trigger characteristics measurement circuit.

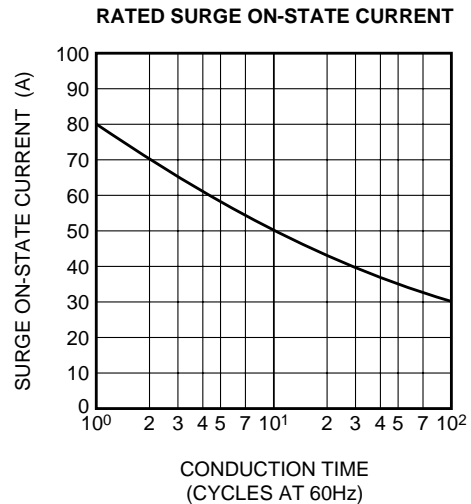
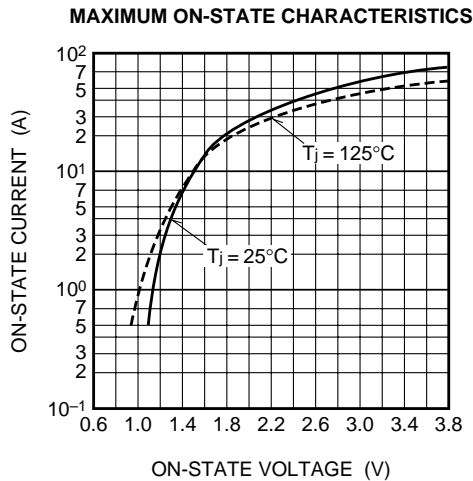
\*3. Case temperature is measured on the T2 terminal.

\*4. The contact thermal resistance R<sub>th (c-f)</sub> in case of greasing is 1.0°C/W.

\*5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature T <sub>j</sub> =125°C  2. Rate of decay of on-state commutating current (di/dt) <sub>c</sub> =-4.0A/ms  3. Peak off-state voltage V <sub>D</sub> =400V	

## PERFORMANCE CURVES

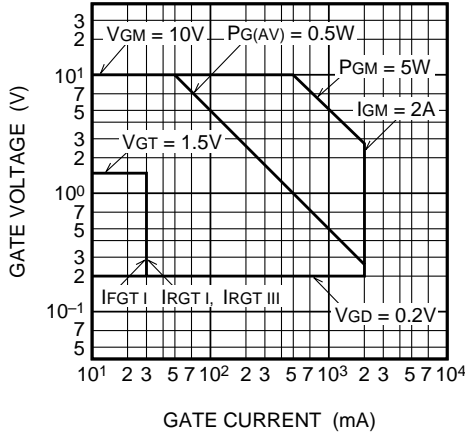


# BCR8CS

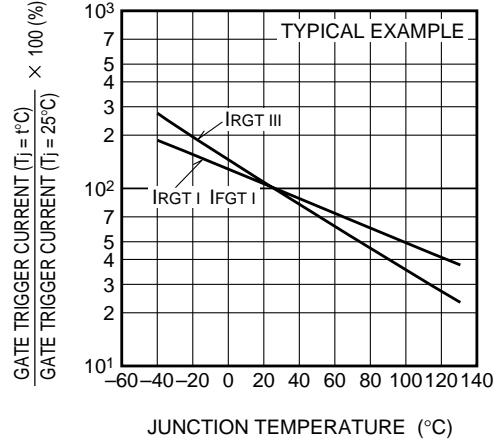
Refer to the page 6 as to the product guaranteed maximum junction temperature 150°C

MEDIUM POWER USE  
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

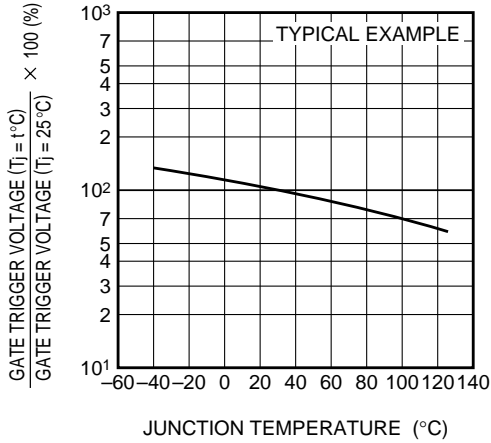
**GATE CHARACTERISTICS (I, II AND III)**



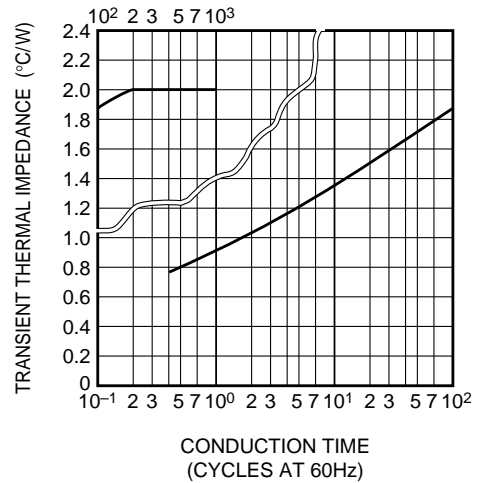
**GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE**



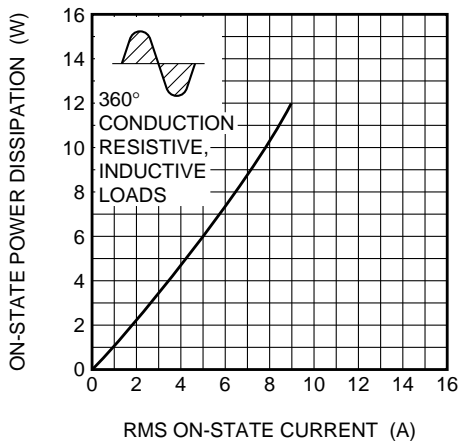
**GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE**



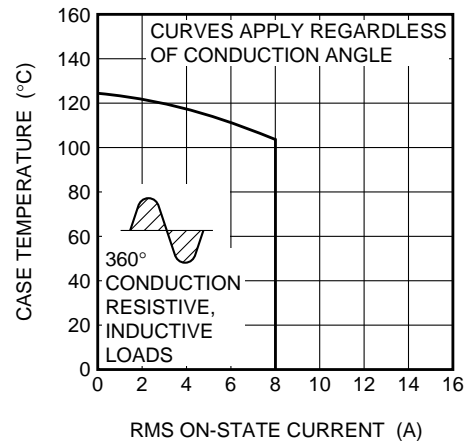
**MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)**



**MAXIMUM ON-STATE POWER DISSIPATION**



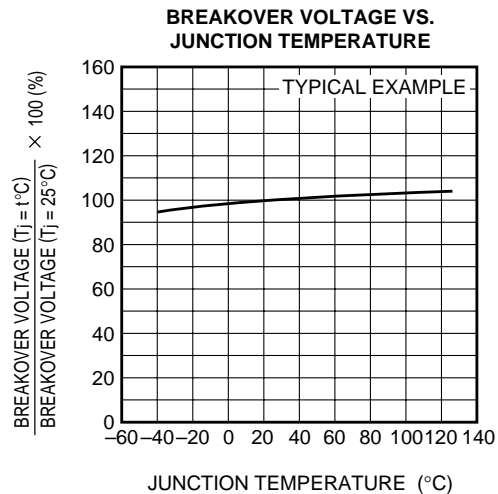
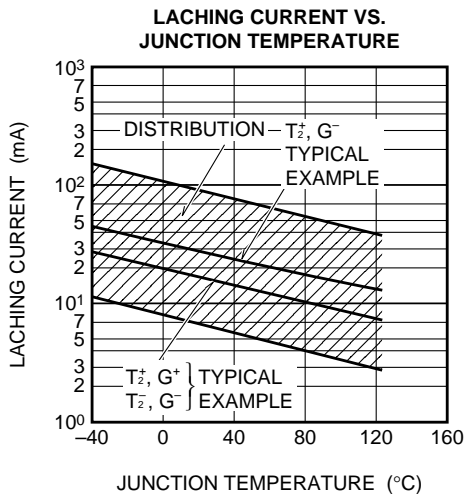
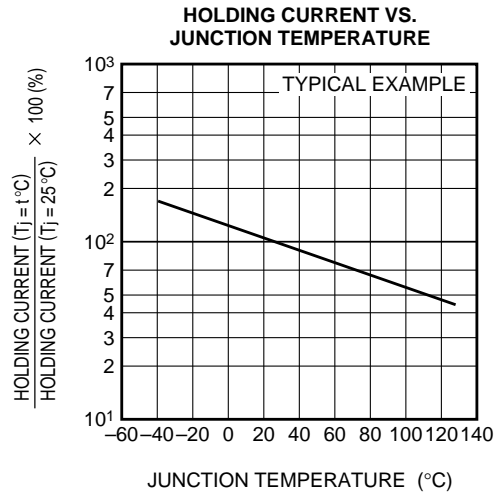
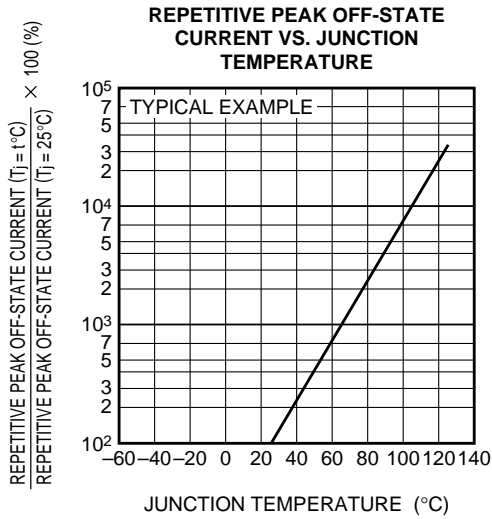
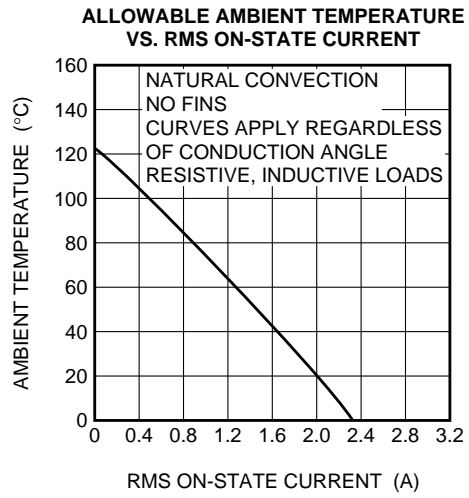
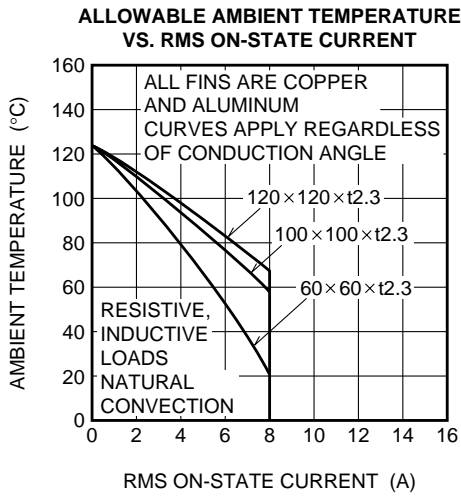
**ALLOWABLE CASE TEMPERATURE VS. RMS ON-STATE CURRENT**



**BCR8CS**

Refer to the page 6 as to the product guaranteed maximum junction temperature 150°C

**MEDIUM POWER USE**  
**NON-INSULATED TYPE, PLANAR PASSIVATION TYPE**

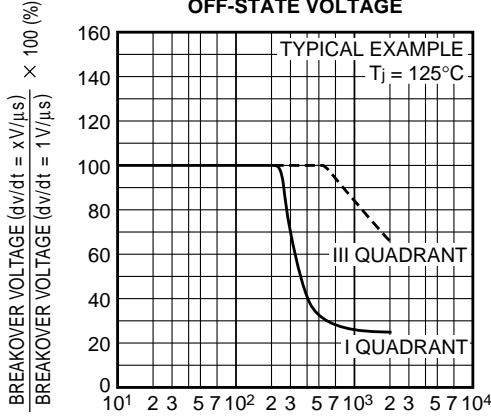


# BCR8CS

Refer to the page 6 as to the product guaranteed maximum junction temperature 150°C

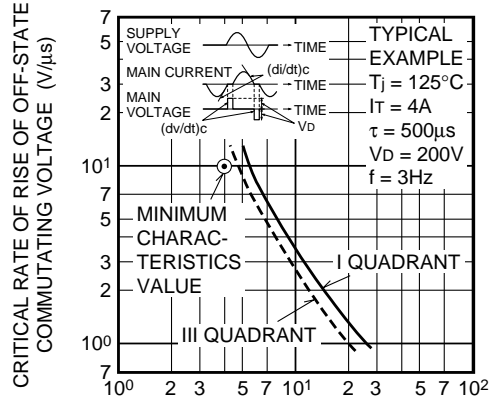
MEDIUM POWER USE  
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

**BREAKEOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE**



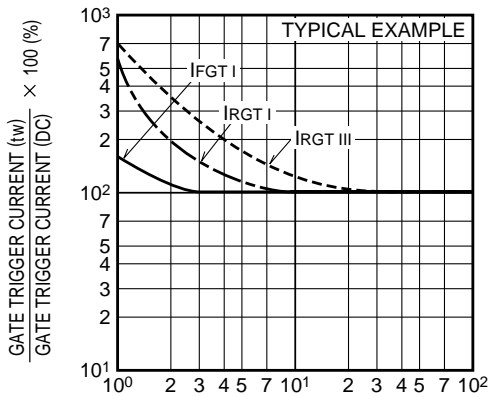
RATE OF RISE OF OFF-STATE VOLTAGE (V/μs)

**COMMUTATION CHARACTERISTICS**



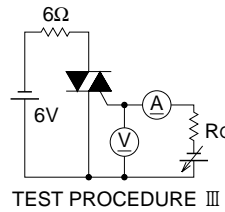
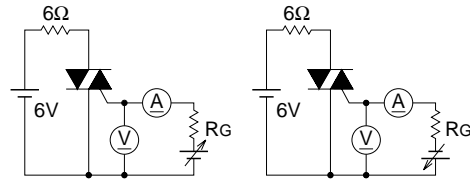
RATE OF DECAY OF ON-STATE COMMUTATING CURRENT (A/ms)

**GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH**



GATE CURRENT PULSE WIDTH (μs)

**GATE TRIGGER CHARACTERISTICS TEST CIRCUITS**




# BCR8CS

MEDIUM POWER USE

NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

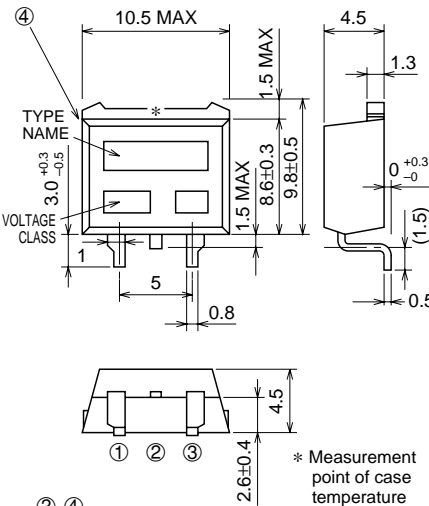
The product guaranteed maximum junction temperature 150°C (See warning.)

**BCR8CS**



- **IT (RMS)** ..... **8A**
- **VDRM** ..... **600V**
- **IFGT I , IRGT I , IRGT III** ..... **20mA**

**OUTLINE DRAWING** Dimensions in mm



① T1 TERMINAL  
② T2 TERMINAL  
③ GATE TERMINAL  
④ T2 TERMINAL

TO-220S

\* Measurement point of case temperature

**APPLICATION**

Solid state relay, hybrid IC

(Warning)

1. Refer to the recommended circuit values around the triac before using.
2. Be sure to exchange the specification before using. If not exchanged, general triacs will be supplied.

**MAXIMUM RATINGS**

Symbol	Parameter	Voltage class		Unit
		12	600	
VDRM	Repetitive peak off-state voltage *1	600		V
VDSM	Non-repetitive peak off-state voltage *1	720		V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, Tc=130°C*3	8	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	80	A
I <sup>2</sup> t	I <sup>2</sup> t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	26	A <sup>2</sup> s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
VGM	Peak gate voltage		10	V
IGM	Peak gate current		2	A
Tj	Junction temperature		-40 ~ +150	°C
Tstg	Storage temperature		-40 ~ +150	°C
—	Weight	Typical value	1.2	g

\*1. Gate open.



# BCR8CS

The product guaranteed maximum junction temperature 150°C (See warning.)

**MEDIUM POWER USE**  
**NON-INSULATED TYPE, PLANAR PASSIVATION TYPE**

## ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDRM	Repetitive peak off-state current	T <sub>j</sub> =150°C, V <sub>DRM</sub> applied	—	—	2.0	mA	
V <sub>TM</sub>	On-state voltage	T <sub>c</sub> =25°C, I <sub>TM</sub> =12A, Instantaneous measurement	—	—	1.5	V	
V <sub>FGT I</sub>	Gate trigger voltage *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	1.5	V
V <sub>RGT I</sub>			II	—	—	1.5	V
V <sub>RGT III</sub>			III	—	—	1.5	V
I <sub>FGT I</sub>	Gate trigger current *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	20	mA
I <sub>RGT I</sub>			II	—	—	20	mA
I <sub>RGT III</sub>			III	—	—	20	mA
V <sub>GD</sub>	Gate non-trigger voltage	T <sub>j</sub> =125°C/150°C, V <sub>D</sub> =1/2V <sub>DRM</sub>	0.2/0.1	—	—	V	
R <sub>th (j-c)</sub>	Thermal resistance	Junction to case *3 *4	—	—	2.0	°C/W	
(dv/dt) <sub>c</sub>	Critical-rate of rise of off-state commutating voltage *5	T <sub>j</sub> =125°C/150°C	10/1	—	—	V/μs	

\*2. Measurement using the gate trigger characteristics measurement circuit.

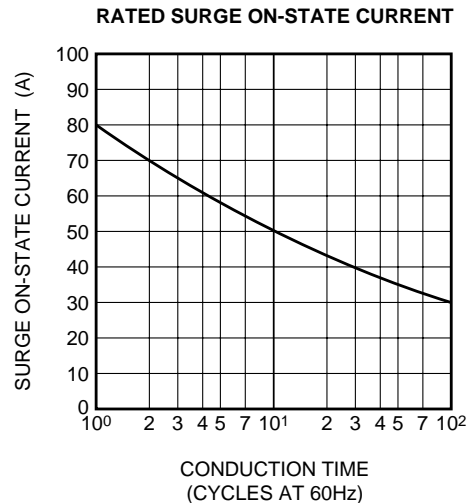
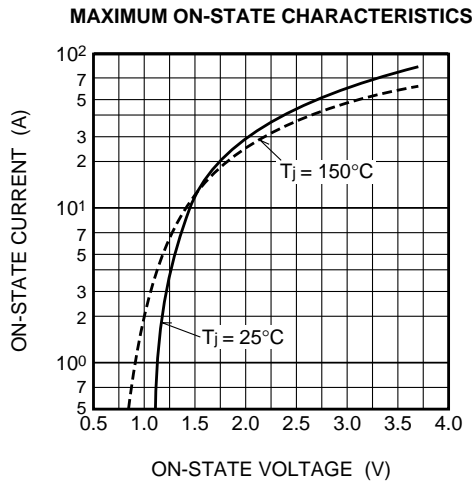
\*3. Case temperature is measured on the T2 terminal.

\*4. The contact thermal resistance R<sub>th (c-f)</sub> in case of greasing is 1.0°C/W.

\*5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature T <sub>j</sub> =125°C/150°C  2. Rate of decay of on-state commutating current (di/dt) <sub>c</sub> =-4.0A/ms  3. Peak off-state voltage V <sub>D</sub> =400V	

## PERFORMANCE CURVES

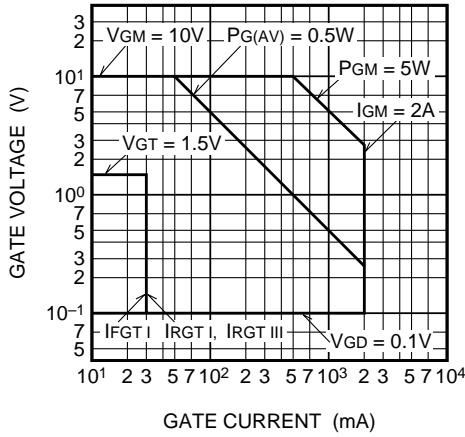


# BCR8CS

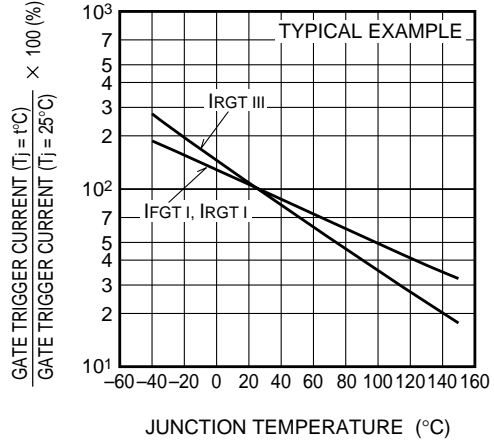
The product guaranteed maximum junction temperature 150°C (See warning.)

**MEDIUM POWER USE**  
**NON-INSULATED TYPE, PLANAR PASSIVATION TYPE**

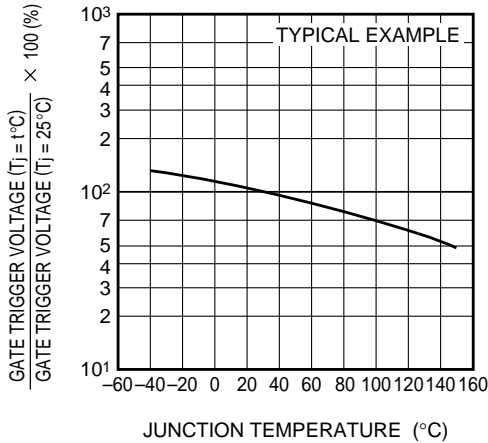
**GATE CHARACTERISTICS (I, II AND III)**



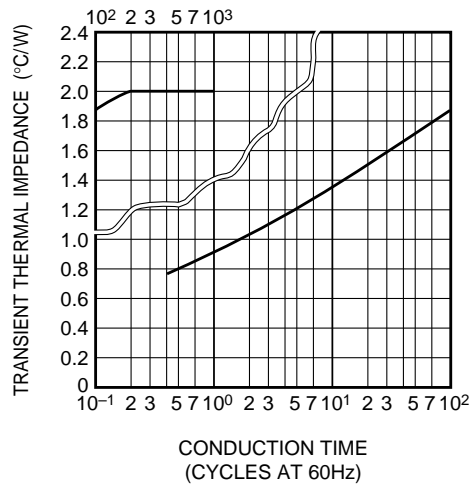
**GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE**



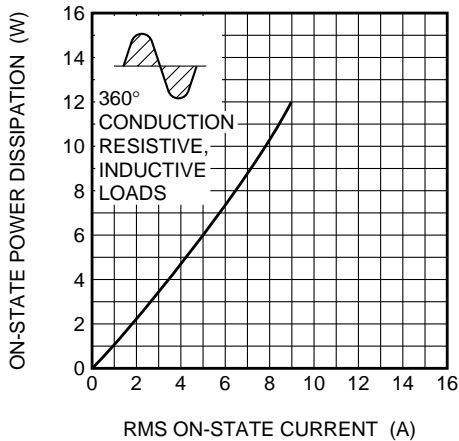
**GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE**



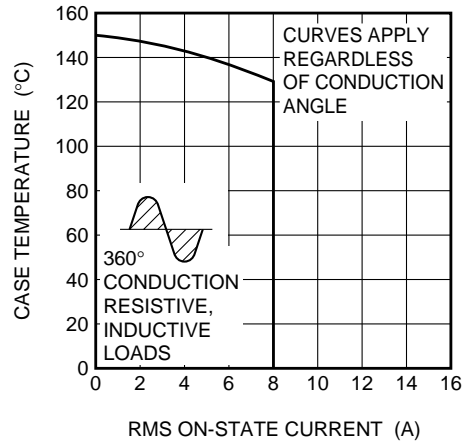
**MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)**



**MAXIMUM ON-STATE POWER DISSIPATION**



**ALLOWABLE CASE TEMPERATURE VS. RMS ON-STATE CURRENT**

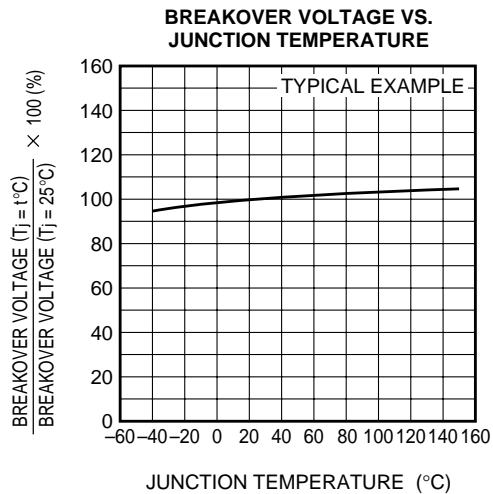
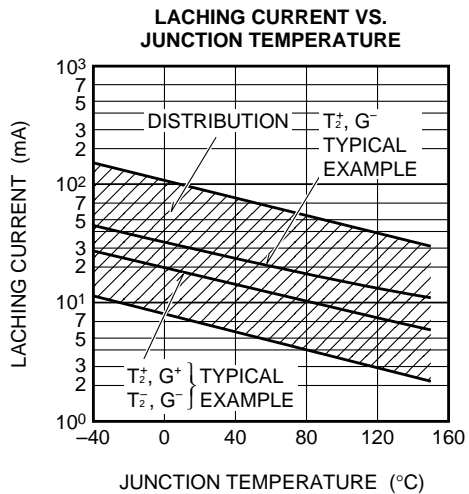
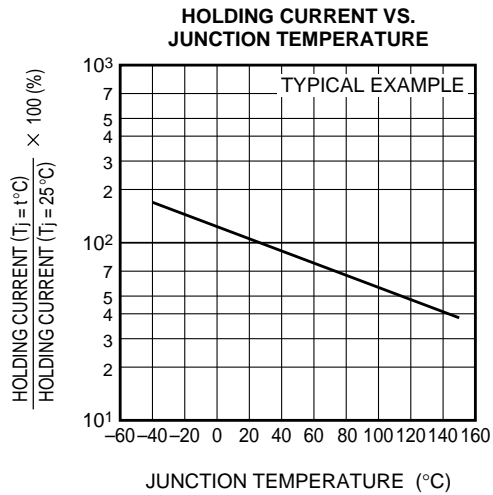
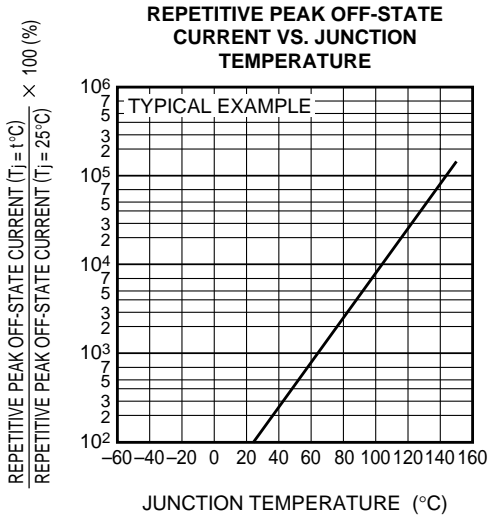
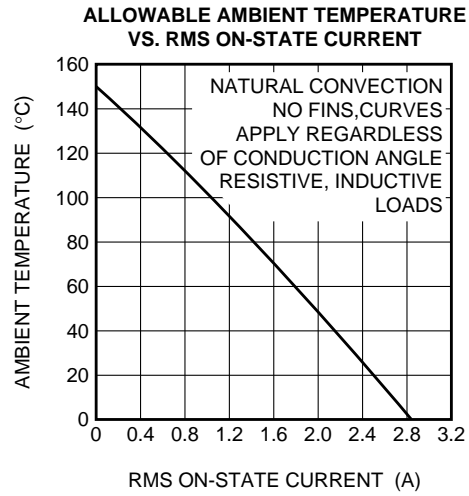
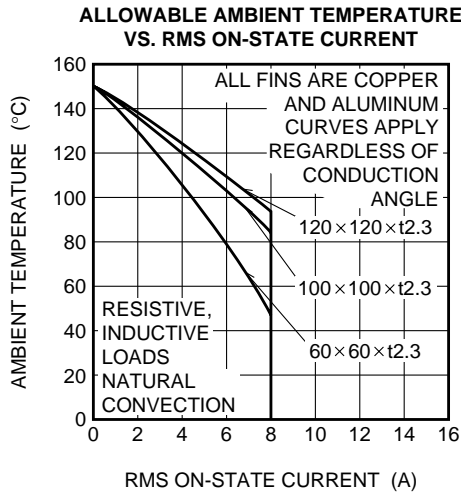




# BCR8CS

The product guaranteed maximum junction temperature 150°C (See warning.)

MEDIUM POWER USE  
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

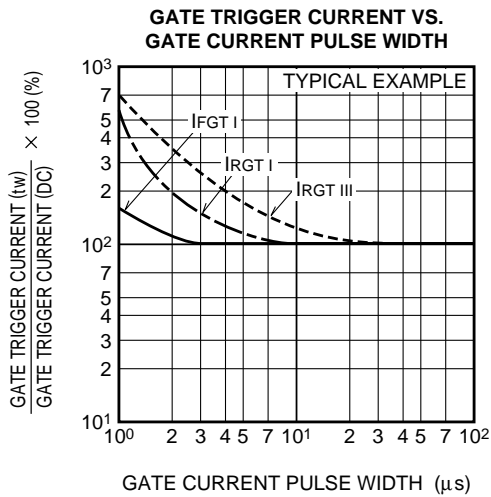
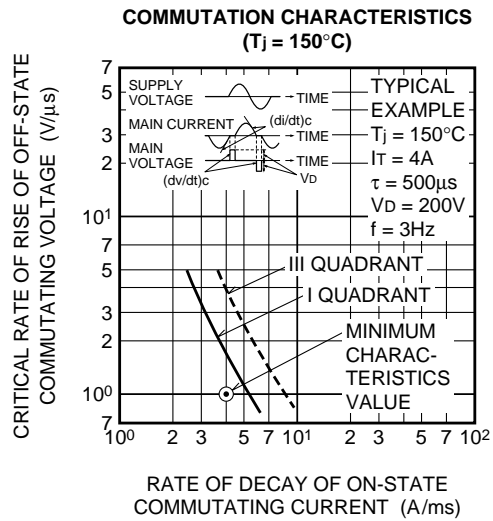
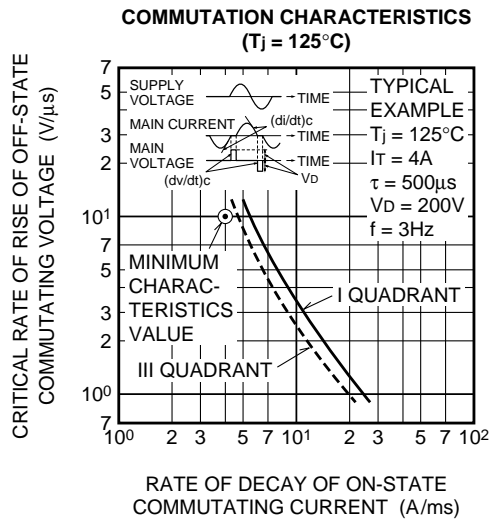
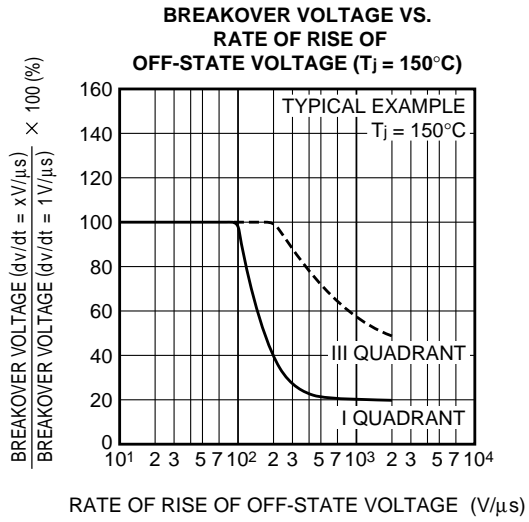
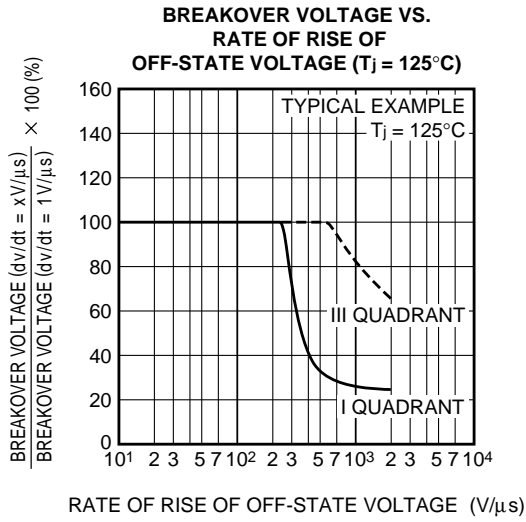


**BCR8CS**

**MEDIUM POWER USE**

**NON-INSULATED TYPE, PLANAR PASSIVATION TYPE**

The product guaranteed maximum junction temperature 150°C (See warning.)

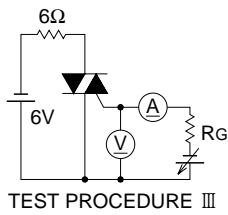
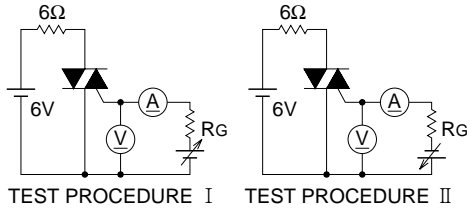


# BCR8CS

The product guaranteed maximum junction temperature 150°C (See warning.)

**MEDIUM POWER USE**  
**NON-INSULATED TYPE, PLANAR PASSIVATION TYPE**

**GATE TRIGGER CHARACTERISTICS TEST CIRCUITS**



**RECOMMENDED CIRCUIT VALUES  
 AROUND THE TRIAC**

